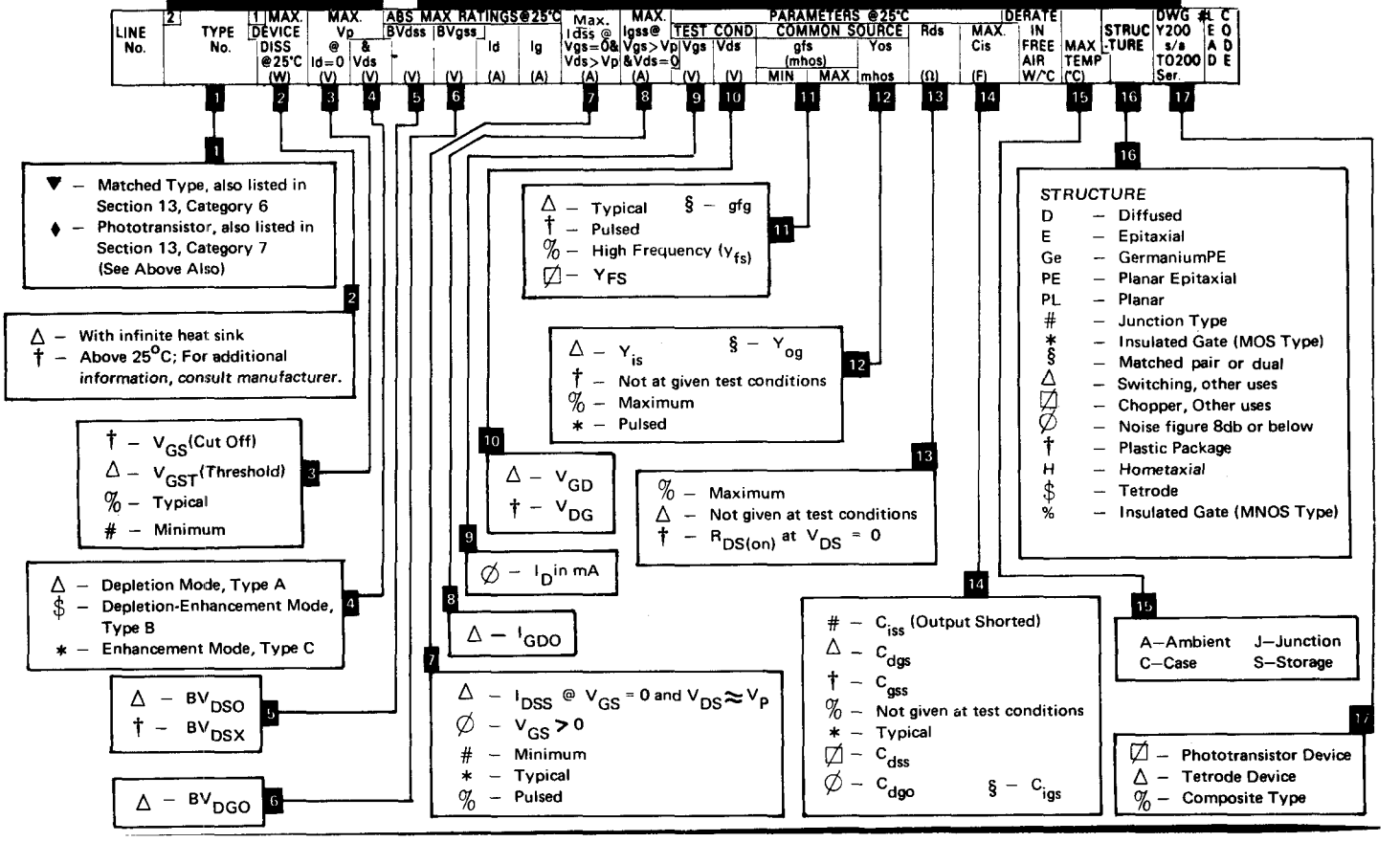
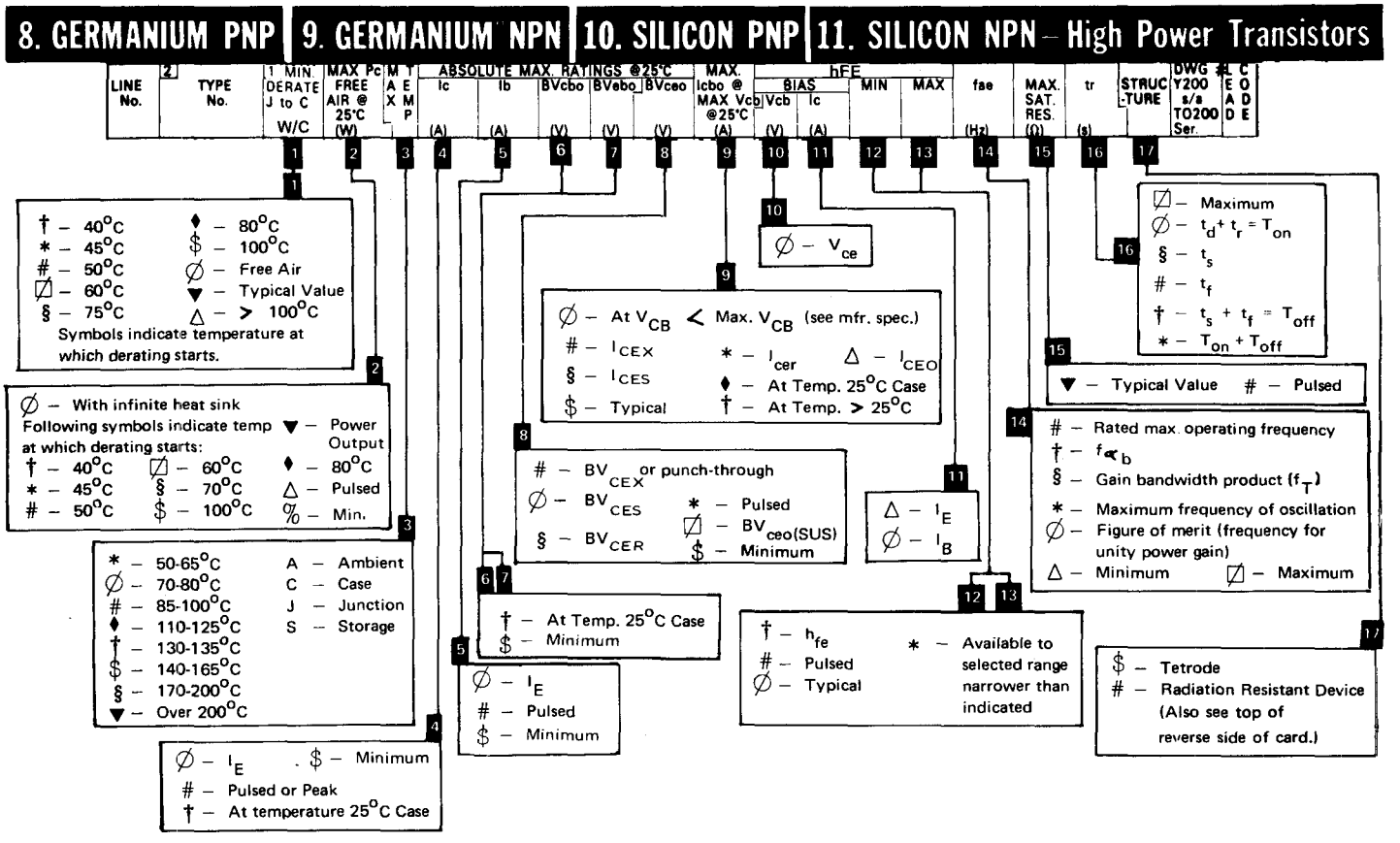
6. "P" Channel — 7. "N" Channel — SILICON FIELD EFFECT TRANSISTORS



8. GERMANIUM PNP — 9. GERMANIUM NPN — 10. SILICON PNP — 11. SILICON NPN – High Power Transistors



7. SILICON FIELD EFFECT TRANSISTORS - N CHANNEL

IN ORDER OF (1) DISSIPATION
(2) TYPE No.

LINE No.	2 TYPE No.	1 MAX. DEVICE DISS @25°C (W)	MAX. Vp @ Id=0 (V)	& Vds (V)	ABS MAX RATINGS@25°C BVdss (V)	BVgss (V)	Id (A)	Ig (A)	MAX. Idss @ Vgs=0& Vds>Vp (A)	MAX. Igss@ Vgs>Vp &Vds=0	TEST COND Vgs (V)	Vds (V)	PARAMETERS @25°C COMMON SOURCE gfs (mhos) MIN	gfs (mhos) MAX	Yos mhos	r(DS) on (Ω)	MAX. Cis (F)	DERATE IN FREE AIR W/°C	MAX TEMP (°C)	STRUC-TURE	DWG Y200 s/a TO200 Ser.	#L C E O A D D E
1#	6G2	300m	3.0	20		30Δ			4.0m		0.0	20	1.0m	2mΔ			7.5p	1.7m	200J	PE	TO72	DH
2	A190	300m	4.0†	15Δ	30	30	10m	5.0m	8.0m	.10n	0.0	15	2.0m	8.0m			5.0p#	1.0m	200S	#	TO72	DH
3	A192	300m	8.0†	15Δ	30	30Δ	20m	10m	20mΔ	500p	0.0	15	3.5m	6.5m	85u		5.0p	1.6m	200J	PE#Ø	TO72	DH
4	A193	300m	6.0†	15Δ	30	30Δ	20m	10m	10mΔ	500p	0.0	15	3.0m	6.5m	50u		5.0p	1.6m	200J	PE#Ø	TO72	DH
5	A390†	300m	5.0Δ	10*	25	35Δ	30m		10n	10p	2.0Ø	10	1.0m			300 †	5.5p	1.6m	200J	*	TO72	DZ
6#	BFS67	300m	6.0	15	50	50	50m	10m	10m	100p	0.0	15	1.5m	6.5m	20u		6.0p		150	PE	u34	
7#	BFS68	300m	8.0	15	30	30	50m	10m	25m	500p	0.0	15	3.5m	6.5m	35u		6.0p		150	PE	u34	
8#	BSV38†	300mΔ	10†	15	25	25	150m	10m	50m#%	250p						25	18p#	2.4m	150S	PEØ	u51	G
9#	BSV39	300mΔ	6.0†	15	25	25	150m	10m	100m%	500p						70	18p#	2.4m	150S	PEØ	u51	G
10#	C80	300m	30	50			10m						.05m	.25m	1.0u				150J		R111	DB
11	CM600	300m	7.0	1.5Δ	3.0Δ	10Δ	100m	100m	50m*%	3.0n	0.0	10	10m†	30m		.06kΔ	6.5pt	2.3m	200J	E#	TO18	DD
12	CM601	300m	10	1.5Δ	3.0Δ	10Δ	100m	100m	50m%	3.0n	0.0	10	10m†	30m		60 Δ	6.5pt	2.3m	200J	E#	TO18	DD
13	CM602	300m	10	1.5Δ	2.0Δ	30Δ	100m	100m	70mΔ%	10n	0.0	10	10m†	30m		40 Δ	6.5pt	2.3m	200J	E#	TO18	DD
14	CM603	300m	1.5	1.5Δ	5.0Δ	15Δ	100m	100m	100mΔ%	3.0n	0.0	10	20m†	60m		30 Δ	6.5pt	2.3m	200J	E#	TO18	DD
15	DN3365A	300m	12	20		40		10m	4.0m	5.0n	0.0	30	.40m	2.0m	50u		15p	2.4m	150C		TO18	DBØ
16	DN3366A	300m	6.5	20		40		10m	1.0m	5.0n	0.0	30	.25m	1.0m	20u		15p	2.4m	150C		TO18	DBØ
17	DN3367A	300m	2.2	20		40		10m	.25m	5.0n	0.0	30	.10m	1.0m	10u		15p	2.4m	150C		TO18	DBØ
18	DN3368A	300m	12	20		40		10m	12m	5.0n	0.0	30	1.0m	4.0m	80u		20p	2.4m	150C		TO18	DBØ
19	DN3369A	300m	6.5	20		40		10m	2.5m	5.0n	0.0	30	.60m	2.5m	30u		20p	2.4m	150C		TO18	DBØ
20	DN3370A	300m	3.2	20		40		10m	.60m	5.0n	0.0	30	.30m	2.5m	15u		20p	2.4m	150C		TO18	DBØ
21	DN3436A	300m	9.8	20		50		10m	15m	.50n	0.0	20	2.5m	10m	35u		18p	1.7m	200C		TO18	DBØ
22	DN3437A	300m	4.8	20		50		10m	4.0m	.50n	0.0	20	1.5m	6.0m	20u		18p	1.7m	200C		TO18	DBØ
23	DN3438A	300m	2.3	20		50		10m	1.0m	.50n	0.0	20	.80m	4.5m	5.0u		18p	1.7m	200C		TO18	DBØ
24	DN3458A	300m	7.8	20		50		10m	15m	.25n	0.0	20	2.5m	10m	35u		18p	1.7m	200C		TO18	DBØ
25	DN3459A	300m	3.4	20		50		10m	4.0m	.25n	0.0	20	1.5m	6.0m	20u		18p	1.7m	200C		TO18	DBØ
26	DN3460A	300m	1.8	20		50		10m	1.0m	.25n	0.0	20	.80m	4.5m	5.0u		18p	1.7m	200C		TO18	DBØ
27	FT0654E	300m	2.5†	20	50	50		50m	4.0mΔ	1.0n	0.0	20	2.0m%	6m%	24u	.30kt	20p#	2.0m	175J	DPL	TO18	DBØ
28	MD1F3458	300m	8.0†	20		50Δ		10m	15m	5.0n	0.0	20	2.5m	10m			18p#		150A	Δ	TO122	GP
29	MD1F3459	300m	4.0†	20		50Δ		10m	4.0m	5.0n	0.0	20	1.5m	6.0m	20u		18p#		150A	Δ	TO122	GP
30	MD1F3460	300m	2.0†	20		50Δ		10m	1.0m	5.0n	0.0	20	800u	4.5m	50u		18p#		150A	Δ	TO122	GP
31	MD1F3823	300m	8.0	15	30Δ	30Δ		10m	20n%	5.0n	0.0	15	3.2m%		35u*		6.0p#		150A		TO122	GP
32	MD1F4416	300m	6.0†	15		30Δ		10m	15m	500u	0.0	15	4.5m	7.5m†	50u		4.0p#		150A		TO122	GP
33	MM2102	300m	4.0Δ	*	25	75	30		10uΔ	10p			1.0m			200	4.5p		200	*	R38y	
34#	PH244N♦	300m	3.0†	15	25	25		10m	30m%	200p	0.0	15	8.0m	15m†			13p#	1.7	200S	PEΔ		
35	SI221N	300m	.30	5.0		8.0Δ			.15m	2.0n	0.0	5.0	.40m	1.2m			30p	2.0m			TO72	DUØ
36	SI222N	300m	.50	5.0		8.0Δ			.30m	2.0n	0.0	5.0	.70m	1.8m			30p	2.0m			TO72	DUØ
37	SI223N	300m	.70	5.0		8.0Δ			.60m	2.0n	0.0	5.0	1.0m	2.4m			30p	2.0m			TO72	DUØ
38	SI224N	300m	1.0	5.0		8.0Δ			1.5m	2.0n	0.0	5.0	1.6m	3.6m			30p	2.0m			TO72	DUØ
39	SI225N	300m	1.5	5.0		8.0Δ			3.0m	2.0n	0.0	5.0	2.2m	5.0m			30p	2.0m			TO72	DUØ
40	SI226N	300m	2.5	5.0		8.0Δ			6.0m	2.0n	0.0	5.0	3.0m	7.0m			30p	2.0m			TO72	DUØ
41#	SI244N	300m	3.0†	15	25	25		10m	30m%	200p	0.0	15	8.0m	15m†		100 %	13p#	1.7	200S	PEΔØ	TO18	DBØ
42#	SI245N	300m	5.0†	15	25	25		10m	35m%	200p						80 %	13p#	1.7	200S	PEΔØ	TO18	DBØ
43#	SI246N	300m	10†	15	25	25		10m	75m%	200p						60 %	13p#	1.7	200S	PEΔØ	TO18	DBØ
44	SU2076▼	300m	3.0	10		50Δ			10u	250p	.70Ø	10†	1.5m		20u		18p	1.7m	200J	Ø	L21	
45	SU2077▼	300m	3.0	10		50Δ			10u	250p	.70Ø	10†	1.5m		20u		18p	1.7m	200J	Ø	L21	
46	SU2078▼	300m	4.0	10		50Δ			2.0m	.25n	.2Ø	10†	.30m		5.0u		7.0p	1.7m	200J		L21	
47	SU2079▼	300m	4.0	10		50Δ			2.0m	.25n	.2Ø	10†	.30m		5.0u		7.0p	1.7m	200J		L21	
48	u89Ø	300m	6.0	10		20	50m		5.0mΔ	10n	0.0	10		1.2mΔ				2.0m	150S	D	R38q	
49	u205▼	300m	4.0	20		50		50m	7.0m	25p	0.0	20	1.0m	4.0m			6.0p#	1.7m	200S	#	TO71	
50	u206▼	300m	4.0	20		50		50m	7.0m	25p	0.0	20	1.0m	4.0m			6.0p#	1.7m	200S	#	TO71	
51	u207▼	300m	4.0	20		50		50m	7.0m	25p	0.0	20	1.0m	4.0m			6.0p#	1.7m	200S	#	TO71	
52	U203	300m	5.0	15		30		50m	2.0m	1.0n	0.0	15	300u	2.0m	50u%		6.0p#	2.0m	200S	ØΔ	TO72	
53	U204	300m	5.0	15		30		50m	2.0m	1.0n	0.0	15	300u	2.0m	50u%		6.0p#	2.0m	200S	ØΔ	TO72	
54	U205▼	300m	4.0	20		50		50m	7.0m	.02n	0.0	20	1.0m	4.0m			6p#	1.7m	200S	#	TO71	
55	U206▼	300m	4.0	20		50		50m	7.0m	.02n	0.0	20	1.0m	4.0m			6p#	1.7m	200S	#	TO71	
56	U207▼	300m	4.0	20		50		50m	7.0m	.02n	0.0	20	1.0m	4.0m			6.0p#	1.7m	200S	#	TO71	
57	U2047E	300m	8.0†	15	30	30	30m		25m	250p	0.0	15	4.5m		50u%		4.0p#	2.5m	125J	Ø	R97b	DD
58	UC105	300m	5.0	20		30		10m	7.5m	100p	0.0	20	2.0m			600 †	5.0p%		200J	PL	TO18	DD
59	UC120	300m	1.7	20		30		10m	1.2m	100p	0.0	20	1.0m			1.2kt	5.0p%		200J	PL	TO72	DH
60	UC125	300m	1.7	20		30		10m	1.2m	100p	0.0	20	1.0m			1.2kt	5.0p%		200J	PL	TO18	DD
61	UC135	300m	1.2	20		30		10m	500u	100p	0.0	20	500u			2.4kt	5.0p%		200J	PL	TO18	DD
62	UC258	300m	3.0†	15		30		50m	30m	100p	10Ø	15	12m	24m	50u		14p#	1.7m	200J	PLØ	TO72	
63	UC701	300m	6.0	15		40			3.0m	200p										PE	TO72	
64	UC750	300m	6.0	15		30			50u#	2.0n										PE	TO18	
65	UT100	300m	6.0	10		25		10m	30m	100p	10Ø	10	6.0m	10m	200u§		5.0p§	1.7m	150A	#	u77	EE
66	UT101	300m	6.0	10		25		10m	30m	100p	10Ø	10	6.0m	10m	200u%		5.0p#	1.7m	150A	#	u77a	EF
67	HSC4391†	310m	10	20	40	40		50m	150m%	100p						30 %	14p#	3.1m	125J	E#	TO106	DB
68	HSC4392†	310m	5.0	20	40	40		50m	75m%	100p						60 %	14p#	3.1m	125J	E#	TO106	DB
69	HSC4393†	310m	3.0	20	40	40		50m	30m%	100p						100 %	14p#	3.1m	125J	E#	TO106	DB
70	HSC4416	310m	6.0	15	30	30		10m	15m	100p	0.0	15	4.5m%	7.5m%	50u%		4.0p#	3.1m	125J	E#	TO106	DB
71	HSC4416A	310m	6.0	15	35	35		10m	15m	100p	0.0	15	4.5m%	7.5m%	50u%		4.0p#	3.1m	125J	E#	TO106	DB
72	HSC5163	310m	8.0	15	25	25		50m	40m	10n	0.0	15	2.0m	9.0m	200u%	500 %	12p#	3.1m	125J	E#	TO106	DB
73	HSC5457	310m	6.0	15		25			5.0m%	1.0n	0.0	15	1.0m	5.0m	50u*		7.0p#	3.1m	125J	E#	TO106	DB
74	HSC5457A	310m	6.0	15		50			5.0m%	1.0n	0.0	15	1.0m	5.0m	50u*		7.0p#	3.1m	125J	E#	TO106	DB
75	HSC5458	310m	7.0	15		25			9.0m%	1.0n	0.0	15	1.5m	5.5m	50u*		7.0p#	3.1m	125J	E#	TO106	DB
76	HSC5458A	310m	7.0	15		50			9.0m%	1.0n	0.0	15	1.5m	5.5m	50u*		7.0p#	3.1m	125J	E#	TO106	DB
77	HSC5459	310m	8.0	15		25			16m%	1.0n	0.0	15	2.0m	6.0m	50u*		7.0p#	3.1m	125J	E#	TO106	DB
78	HSC5459A	310m	8.0	15		50			1.6m%	1.0n	0.0	15	2.0m	6.0m	50u*		7.0p#	3.1m	125J	E#	TO106	DB
79	HSC5484	310m	3.0			25		10m	5.0m	1.0n	0.0	15	3.0m	6.0m	50u		4.0p#	3.1m	125J	E#	TO106	DB
80	HSC5485	310m	4.0			25		10m	10m	1.0n	0.0	15	3.5m	7.0m	60u		4.0p#	3.1m	125J	E#	TO106	DB
81	HSC5486	310m	6.0			25		10m	20m	1.0n	0.0	15	4.0m	8.0m	75u		4.0p#	3.1m	125J	E#	TO106	DB
82	HSC5638†	310m	12			30			50m	1.0n						30 %	10p#	3.1m	125J	E#	TO106	DB
83	HSC5639†	310m	8.0			30			25m	1.0n						60 %	10p#	3.1m	125J	E#	TO106	DB
84	HSC5640†	310m	6.0			30			5.0m	1.0n						100 %	10p#	3.1m	125J	E#	TO106	DB
85#	ZFT12	350m	2.4	20	25	25				10nΔ	0.0	20	400u	1.0m					150J	PL$	TO33	DY
86#	ZFT12A	350m	2.4	20	25	25				30nΔ	0.0	20	400u	1.0m					150J	PL$	TO33	DY
87#	ZFT14	350m	7.9	20	25	25				10nΔ	0.0	20	900u	2.0m					150J	PL$	TO33	DY
88#	ZFT14A	350m	7.9	20	25	25				30nΔ	0.0	20	900u	2.0m					150J	PL$	TO33	DY
89#	ZFT16	350m	5.0%	20	50	10			10m	10n	0.0	20	3.0mΔ			300 †	30p*		150J	PL	TO33	
90#	ZFT18	350m	5.0%	20	100	10			10m	10n	0.0	20	3.0mΔ			300 †	30p*		150J	PL	TO33	
91	LDF603	360m	8.0†	15Δ	20	20	30m	10m	8.0m	500p	0.0	15	1.0m	4.0m	150u%		5.0p#	2.9m	150J	Ø	TO122	DB
92	LDF604	360m	8.0†	15Δ	20	20	30m	10m	12m	500p	0.0	15	2.5m	5.5m	150u%		5.0p#	2.9m	150J	Ø	TO122	DB
93	LDF605	360m	8.0†	15Δ	20	20	30m	10m	20m	500p	0.0	15	3.0m	7.0m	150u%		5.0p#	2.9m	150J	Ø	TO122	DB
94	LDF691†	360m	10†	20Δ	30	30		50m		.50n	0.0	20				.03k	16p	2.9m	150J	Ø	u34	DB
95	LDF692†	360m	5.0†	20Δ	30	30		50m		.50n	0.0	20				.06k	16p	2.9m	150J	Ø	u34	DB
96	LDF693	360m	3.0†	20Δ	30	30		50m		500u	0.0	20				100	16p	2.9m	150J	Ø	u34	DB
97#	NKT80211	360m	.50	5.0		10		10m	.15m	10n	0.0	5.0	.20m	.70m		.40k	23p	1.8m	200	#	TO18	DB
98#	NKT80212	360m	.70	5.0		10		10m	.30m	10n	0.0	5.0	.40m	1.1m		.40k	23p	1.8m	200	#	TO18	DB
99#	NKT80213	360m	1.0	5.0		10		10m	.60m	10n	0.0	5.0	.60m	1.5m		.40k	23p	1.8m	200	#	TO18	DB
100#	NKT80214	360m	1.5	5.0		10		10m	1.5m	10n	0.0	5.0	.90m	2.2m		.40k	23p	1.8m	200	#	TO18	DB
101#	NKT80215	360m	2.5	5.0		10		10m	3.0m	10n	0.0	5.0	1.3m	3.0m		.40k	23p	1.8m	200	#	TO18	DB
102#	NKT80216	360m	3.5	5.0		10		10m	6.0m	10n	0.0	5.0	1.8m	4.2m		.40k	23p	1.8m	200	#	TO18	DB
103	NPC211N	360m	.50%	5.0	5.0	8.0Δ	200u	90u	150u	10n	0.0	5.0	200m	700m			25p		200J		TO18	DBØ
104	NPC212N	360m	.70%	5.0	5.0	8.0Δ	200u	180u	300u	10n	0.0	5.0	400m	1.1			25p		200J		TO18	DBØ
105	NPC213N	360m	1.0%	5.0	5.0	8.0Δ	200u	400u	600u	10n	0.0	5.0	600m	1.5			25p		200J		TO18	DBØ
106	NPC214N	360m	1.5%	5.0	5.0	8.0Δ	200u	900u	1.5m	10n	0.0	5.0	900m	2.2			25p		200J		TO18	DBØ
107	NPC215N	360m	2.5%	5.0	5.0	8.0Δ	200u	1.8m	3.0m	10n	0.0	5.0	1.3	3.0			25p		200J		TO18	DBØ
108	NPC216N	360m	3.5%	5.0	5.0	8.0Δ	200u	4.0m	6.0m	10n	0.0	5.0	1.8	4.2			25p		200J		TO18	DBØ
109#	SI211N	360m	.50%	5.0		8.0Δ			150u	10n	0.0	5.0	200u	700u			23p*	2.0	200J	PL	TO18	DBØ
110#	SI212N	360m	.70%	5.0		8.0Δ			300u	10n	0.0	5.0	400u	1.1m			23p*	2.0	200J	PL	TO18	DBØ

SYMBOLS AND CODES
EXPLAINED IN INTERPRETER

SYMBOLS & CODES EXPLAINED

SYMBOLS & CODES COMMON TO MORE THAN ONE TECHNICAL SECTION

LINE No.

- ▼ – New Type
- ♦ – Revised Specifications
- # – Non-JEDEC type manufactured outside U.S.A.

TYPE No.

- † – Switching type, also listed in Section 12
- ∅ – Chopper, also listed in Section 13, Category 10
- * – These types also included elsewhere with other characteristics. See Type No. Cross Index for alternate line number.
- § – Radiation Resistant Devices, also listed in Section 13, Category 13.

STRUCTURE (All Sections Except 6 & 7)

A	–	Alloy
AN	–	Annular
D	–	Diffused or drift
DM	–	Diffused mesa
E	–	Epitaxial
EA	–	Epitaxial annular
EM	–	Epitaxial mesa
F	–	Fused
G	–	Grown
GA	–	Gallium Arsenide
H	–	Hometaxial
MA	–	Mico alloy
MD	–	Micro alloy diffused
ME	–	Mesa
MOS	–	Metal oxide silicon
PA	–	Precision alloy
PC	–	Point contact
PD	–	Precision alloy diffused
PE	–	Planar epitaxial
PL	–	Planar
S	–	Surface barrier
*	–	Matched pair
△	–	Switching, other uses
☑	–	Chopper, other uses
∅	–	Noise figure 8db or below
†	–	Plastic package
%	–	Overlay

12. SWITCHING TRANSISTORS

* THESE TYPES ALSO INCLUDED ELSEWHERE WITH OTHER CHARACTERISTICS SEE TYPE NO. CROSS INDEX FOR ADDITIONAL PAGE & LINE NO.

LINE No.	TYPE No.	1 fab (Hz)	2 MAX RISE TIME tr (s)	MAX DELAY TIME td (s)	MAX STORE TIME ts (s)	MAX FALL TIME tf (s)	MAX. Pc IN FREE AIR @ 25°C (W)	BIAS Vcb (V)	BIAS Ie (A)	hFE	MAX. SAT. RES. (Ω)	Cob (F)	r'bb X Cob (s)	DESCRIPTION STRUCTURE P-PNP N-NPN	DESCRIPTION MAT	DESCRIPTION MAX. TEMP (°C)	DESCRIPTION DWG. No.	LEAD CODE
1	3	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15		

1
- † – $f_{\alpha e}$
- § – Gain bandwidth product (f_T)
- * – Maximum frequency of oscillation
- ∅ – Figure of merit (frequency for unity power gain)
- △ – Minimum ☑ – Maximum

2, 3
- $ – Charge storage time constant
- ▼ – Stored base charge – picocoulomb
- ♦ – Total switching time
- ∅ – $T_{on} = t_r + t_d$
- † – Typical Value

4, 5
- ∅ – $T_{off} = t_s + t_f$
- † – Typical Value
- * – $T_{on} + T_{off} = td + tr + tf + ts$

6
- ∅ – With infinite heat sink

Following symbols indicate temperature at which derating starts:

- † – 40°C § – 70°C
- * – 45°C $ – 100°C or greater
- # – 50°C ♦ – 80°C
- ☑ – 60°C △ – Pulsed

7
- ∅ – V_{CE}

8
- ∅ – I_c
- △ – I_B

9
- † – h_{fe}
- # – Pulsed
- △ – Minimum
- ☑ – Maximum
- * – Available to selected range narrower than indicated
- § – Y_{fs} in millimho (FET's only). Bias values are V_{DS} & I_D

10
- § – R_{on} (FET's only)
- # – Pulsed

11
- ☑ – Maximum
- $ – C_{cb}
- § – C_{iss} (FET's only)

12
- † – r'_{bb}

13
- $ – Tetrode
- N – NPN or "N" Channel
- P – PNP or "P" Channel
- § – Field Effect Transistor
- # – Radiation Resistant Device (See above also)

14
- Ge – Germanium
- Si – Silicon

15
- A – Ambient
- C – Case
- J – Junction
- S – Storage

13. MISCELLANEOUS TRANSISTORS

LINE No.	2 TYPE No.	1 CATEGORY USE	CATEGORY STRUCTURE	MAT	DWG. No.	LEAD CODE	DESCRIPTION
		1	2	3			4

1
- 1 – Avalanche Mode
- 2 – Bi-directional
- 3 – Field Effect
- 4 – Hook Collector
- 5 – Complementary Symmetry (PNP & NPN) Matched Pair
- 6 – Matched Pair
- 7 – Phototransistor
- 8 – Tetrode
- 9 – Unijunction: N–N-type emitter (P-type Base) P–P-type emitter (N-type Base)
- 10 – Chopper
- 11 – Unmatched Composite (Dual)
- 12 – Cryogenic
- 13 – Radiation Resistant Devices
- 14 – Pressure Sensitive
- 15 – Transistor chips
- 16 – Darlington
- 17 – Microwave

2
- N – NPN or N Channel
- P – PNP or P Channel (See above also)

3
- Ge – Germanium
- Si – Silicon

4
- See "TECHNICAL TERM DEFINITIONS" Section

13. MISCELLANEOUS TRANSISTORS

IN ORDER OF (1) CATEGORY & (2) TYPE No.

LINE No.	2 TYPE No.	1 CATEGORY USE	STRUCTURE	MAT	DWG # Y200 s/a TO200 Ser.	LEAD CODE	DESCRIPTION
1	SA2738*	6	N	Si	L2t		Pt-.6W;hFE1/2-.90 min;VBE(1-2)-1.5mV max;ΔVBE(1-2)/ΔT-3uV/deg.C.
2	SA2739*	6	N	Si	L2t		Pt-.6W;hFE1/2-.90 min;VBE(1-2)-2.5mV max;ΔVBE(1-2)/ΔT-5uV/deg.C.
3	SD5010*	6	P-MOSØ	Si	L53		Pt 325mW(each side) at 25°C Case temp;yfs 1/2 800m min;VGS(1-2) 70mV.
4	SD5011*	6	P-MOSØ	Si	L54		Pt 325mW(each side) at 25°C Case temp;yfs 1/2 800m min;VGS(1-2) 70mV.
5	SD5012*	6	P-MOSØ	Si	L53		Pt 325mW(each side) at 25°C Case temp;yfs 1/2 800m min;VGS(1-2) 70mV.
6	SD5013*	6	P-MOSØ	Si	L54		Pt 325mW(each side) at 25°C Case temp;yfs 1/2 800m min;VGS(1-2) 70mV.
7	SD5014*	6	P-MOSØ	Si	L53		Pt-325mW(each side) at 25°C case temp;yfs 1/2 .80min;VGS 1/2-200mV max.
8	SD5015*	6	P-MOSØ	Si	L54		Pt-325mW(each side) at 25°C case temp;yfs 1/2 .80min;VGS 1/2-200mV max.
9	SD5050*	6	N-MOSØ	Si	L53		Pt-325mW(each side) at 25°C casetemp;yfs 1/2 .80min;VGS 1/2-200mV max.
10	SD5051*	6	N-MOSØ	Si	L54		Pt-325mW(each side) at 25°C case temp;yfs 1/2 .80min;VGS 1/2-200mV max.
11#	SL360	6	NPN	Si	L44a		BVCBO 15V min;BVCEO 8V min;hFE 30 min;VCE(sat) 400mV max;Ic 10uA.
12	SMT100	6	P	Si	L17a		BVCEO-45V;IC-30mA max;Pt-.60W;VBE(1-2)-20mV;Cob-6.0pf.
13	SMT101	6	P	Si	L17a		BVCEO-45V;IC-30mA max;Pt-.60W;VBE(1-2)-20mV;Cob-6.0pf.
14	SMT102	6	P	Si	L17a		BVCEO-45V;IC-30mA max;Pt-.60W;VBE(1-2)-10mV;hFE1/hFE2-.80 min.
15	SMT103	6	P	Si	L17a		BVCEO-45V;IC-30mA max;Pt-.60W;VBE(1-2)-10mV;hFE1/hFE2-.80 min.
16	SMT104	6	P	Si	L17a		BVCEO-45V;IC-30mA max;Pt-.60W;VBE(1-2)-5.0mV;hFE1/hFE2-.90 min.
17	SMT105	6	P	Si	L17a		BVCEO-45V;IC-30mA max;Pt-.60W;VBE(1-2)-5.0mV;hFE1/hFE2-.90 min.
18	SP8300	6	N-PL	Si	L8a		Pc-.30W;BVCBO-40V;hFE-30 min/IC-10mA;ICBO-.025uA max.
19	SP8302	6	N-PL	Si	L8a		Pc-.50W;BVCBO-100V;hFE-75 min/IC-10mA;ICBO-.025mA max.
20	SP8303	6	N-PL	Si	L8a		Pc-.50W;BVCBO-100V;hFE-35 min/IC-10mA;ICBO-.025mA max.
21	SP8304	6	N-PL	Si	L8a		Pc-.30W;BVCBO-40V;hFE-30 min/IC-10mA;ICBO-.025uA max.
22	SP8307	6	P-PL	Si	L8a		Pc-.30W;BVCBO-20V;hFE-35 min/IC-10mA;ICBO-.01uA max.
23	SP8309	6	N-PL	Si	L8a		Pc-.50W;BVCBO-75V;hFE-40 min/IC-150mA;ICBO-.01uA max.
24	SP8310	6	N-PLØ	Si	L8a		Pc-.50W;BVCBO-75V;hFE-100 min/IC-150mA;ICBO-.01uA max.
25	SP8311	6	N-PL	Si	L8a		Pc-.50W;BVCBO-120V;hFE-40 min/IC-150mA;ICBO-.01uA max.
26	SP10801	6	N-DPL	Si	TO89		hFE1/hFE2-0.8minΔ VBE1-VBE2-1.6mV max,NF-4.0db max
27	SP10810	6	P-DPE	Si	TO89		hFE1/hFE2-0.8minΔ VBE1-VBE2-4.0mV max,hFE-35min at 10mA-1.0V
28	SU2074*	6	N	Si	L21		Pt-300mW; gm1/2-.95 min;VGS(1-2)-15mV max;ΔVGS(1-2)/ΔT-10uV/Deg.C.
29	SU2075*	6	N	Si	L21		Pt-300mW; gm1/2-.95 min;VGS(1-2)-15mV max;ΔVGS(1-2)/ΔT-15uV/Deg.C.
30	SU2076*	6	N	Si	L21		Pt-250mW; gm1/2-.95 min;VGS(1-2)-15mV max;ΔVGS(1-2)/ΔT-10uV/Deg.C.
31	SU2077*	6	N	Si	L21		Pt-250mW; gm1/2-.95 min;VGS(1-2)-15mV max;ΔVGS(1-2)/ΔT-25uV/Deg.C.
32	SU2078*	6	N	Si	L21		Pt-250mW;gm 1/2-.95min;VGS(1-2)-15mV max;ΔVGS(1-2)/ΔT-35uV/Deg. C.
33	SU2079*	6	N	Si	L21		Pt-250mW; gm1/2-.95 min;VGS(1-2)-15mV max;ΔVGS(1-2)/ΔT-60uV/Deg.C.
34#	TA-M93	6	NPN		TO5		Dual 2N930;10% hFE match;5.0mV VBE match;hFE at 10uA-50 min.
35	U205*	6	N	Si	TO71		Pt-.30W;IG(1-2)-5.0nA max;VGS(1-2)-5.0mV max;gfs1/2-.95 min.
36	U206*	6	N	Si	TO71		Pt-.30W;IG(1-2)-5.0nA max;VGS(1-2)-10mV max;gfs1/2-.95 min.
37	U207*	6	N	Si	TO71		Pt-.30W;IG(1-2)-5.0nA max;VGS(1-2)-15mV max;gfs1/2-.95 min.
38	UD1000	6	P-PE	Si	L38		Pt(Both Sides)-200mW;BVCBO-50V;Vo(1-2)-100uV max;IB and IC-20mA.
39	UD2000	6	P-PE	Si	L2n		Pt-400mW;BVCBO-50V;VBE1/2-5mV max;hFE1/2-.90 min;ΔVBE1-2-10uV/degC
40	JAN1N4378	7	NΔ	Si	X69		Pt-50mW;ID-10nAmax;IL-9.0mAmax;tr-1.5uSmax;VCE-50V;VEC-8V.
41	2N318	7	P-A	Ge			Pc-50mW; VCE-12V max; Sens.-25uA/ft can;fab-750kc.
42	2N577	7	P	Ge			Pt-25mW; IC-10mA; Idark-300uA; Photosens-.30A/lumen.
43	800	7	N-G	Ge			Max. Coll. Dist. 65mW; BVCE 20V; IC 5.0mA; Max. Temp. 75 deg.C.A.
44#	BPX30	7	NΔ	Si	X8	AØ	Pt-500mW;ICE(D)-1.0uA max;Sens-100mA/mW/cm2;tr-3.0usec;tf-3.0usec.
45#	BPX59	7	NΔ	Si	X8k	AØ	Darlington;Pt 200mW;Ic 5.0mA at EA 100lx;tr 200us;tf 150us;Max spectral Sens 780nm.
46#	BPY62	7	N-PE	Si	X8a	A§	Pt-.20W;IC-1.0mA min. at B-1000 lux;Sens.-1.0uM;VCE-15V.
47#	BPY66	7	N-DPL	Si	X52		ID-.10uA max;IL-.80mA min;BVCEO-5.0V min.
48	CLR2090	7	N-PEΔ	Si	L3k		Darlington;Pd 250mW;BVCEO 40V min;IL 600uA min at 20uW/cm sq;tr 100us;tf 150us.
49	CLR2191	7	N-PEΔ	Si	L3k		Darlington;Pd 250mW;BVCEO 40V min;IL 4.0mA min at 20uW/cm sq;tr 100us;tf 150us.
50	CLT4160	7	N-PEΔ	Si	u85a		Pd 50mW;BVCEO 50V;BVECO 5.0V, IL 3.0mA max;ID 10nA max;tr 1.5us typ;tf 1.5us typ.
51	CLT4170	7	N-PEΔ	Si	u85a		Pd 50mW;BVCEO 40V;BVECO 5.0V, IL 5.0mA max;ID 10nA max;tr 1.5us typ;tf 1.5us typ.
52	EIP	7	P	Ge			Idk-10uA; Ilt-10mA; Sens.-300uA/1m.
53	EP120	7	P§	Si	R110c	DB	Pt 250mW;Sin 400nA/mW/cm sq;IG(DARK) 30pA max;Igss(DARK) 500pA max;Vp 10V max.
54	EP121	7	P§	Si	R110c	DB	Pt 250mW;Sin 400nA/mW/cm sq;IG(DARK) 30pA max;Igss(DARK) 500pA max;Vp 1.5V max.
55	EP122	7	P§	Si	R110c	DB	Pt 250mW;Sin 400nA/mW/cm sq;IG(DARK) 30pA max;Igss(DARK) 500pA max;Vp 4.0V max.
56	EP123	7	P§	Si	R110c	DB	Pt 250mW;Sin 400nA/mW/cm sq;IG(DARK) 30pA max;Igss(DARK) 500pA max;Vp 10V max.
57#	ES3501	7	P-A	Ge	R71		Pc-36mW at 45 deg. C;BVCBO-10V; Ic-10mA max;Photosens-20uA/fc.
58#	ES3511	7	P-A	Ge	R88		Pc-50mW; BVCBO-25V; IC-20mA max; Photosens-1.0uA/Lux
59	FF400*	7	N-EΔ	Si	TO72	DH	IG(Light)-15nA/FC min;ID(Light)-30uA/FC typ;tr-30ns;tf-50ns.
60	FPM100	7	N-PL	Si	X52		Pt-75mW max;ID-.10uA max;IL-.80mA max;BVCEO-5.0V min.
61	FPN100	7	N-PL	Si			Phototrans;Pd-75mW;ID-.10uA max;IL1-.80mA min.
62	FPO100	7	N-PL	Si	X52a		Pt-75mW max;ID-.10uA max;IL-.80mA. max.
63	FPT100	7	N-PLΔ		R124	A	Pt-100mWmax;ID-101nAmax;IC-25mA;tr-3.0usec.
64	FSP5	7	N-PL	Si	X8		Pc-.50W max; BVCBO-100V; Photo-Sens-1.0ua/fc min.
65	GS100	7	N-PLΔ	Si	u54		Pt-50mW;IL-1.0mA min;ID-1.0nA;VCE (SAT)-.30V;tr-7.0us max;tf-40us max.
66	GS102	7	N-PLΔ	Si	u54		Pt-50mW;IL-.10mA min;ID-1.0nA;VCE (SAT)-.30V;tr-7.0us max;tf-40us max.
67	GS170	7	N-PLΔ	Si	u54		Pt-50mW;IL-1.0mA min;ID-20nA;VCE (SAT)-.30V;tr-7.0us max;tf-40us max.
68	GS172	7	N-PLΔ	Si	u54		Pt-50mW;IL-.10mA min;ID-20nA;VCE (SAT)-.30V;tr-7.0us max;tf-40us max.
69	GS300	7	N-PLΔ	Si	X90a		Pt-50mW;IL-1.0mA min;ID-1.0nA;VCE (SAT)-.30V;tr-7.0us max;tf-40us max.
70	GS302	7	N-PLΔ	Si	X90a		Pt-50mW;IL-.10mA min;ID-1.0nA;VCE (SAT)-.30V;tr-7.0us max;tf-40us max.
71	GS370	7	N-PLΔ	Si	X90a		Pt-50mW;IL-1.0mA min;ID-20nA;VCE (SAT)-.30V;tr-7.0us max;tf-40us max.
72	GS372	7	N-PLΔ	Si	X90a		Pt-50mW;IL-.10mA min;ID-20nA;VCE (SAT)-.30V;tr-7.0us max;tf-40us max.
73	GS600L	7	N-PLΔ	Si	X29		Pt-.25W; IL-30mA; ID-10nA; VCE-10V max; Sens-75uA/fc
74	GS601	7	N-PLΔ	Si	X29		Pt-.25W; IL-20mA; ID-20nA; VCE-5.0V max; Sens-50uA/fc
75	GS611	7	N-PLΔ	Si	X29		Pt-.25W; IL-3.0mA;ID-(12V)-1.0nA;VCE-12V max;Sens-7.5uA/fc
76	GS614	7	N-PLΔ	Si	X29		Pt-150mW;IL-5.0mA min;ID-1.0nA;VCE (SAT)-.30V;tr-1.5us max;tf-2.0us max.
77	GS660	7	N-PLΔ	Si	X29		Pt-.25W; IL-40mA; ID-10nA; VCE-5.0V max; Sens-100uA/fc
78	HPA4202	7	N	Si	X40		BVCEO-25V; fae-120Kc; Cob-9.0pf; hFE-400 typ.
79	ME510	7	N-PE	Si	TO18		BVCBO-10V; Photosens-2.0ua/fc min. at VCE-5.0V, IB-0.0
80	MRD100*	7	NANtΔ	Si	u43	B	Pd-50mW;BVCBO-80V;BVCEO-40V;ICEO(dark)-100nAmax;Sens.Rad.CEO-100nA/mW/sq.cm.
81	MRD200	7	N-AN	Si	X83		Pt-.05W;ICEO(dark)-25nA;BVCEO-50V;Sens.-2.0uA/lum/ft.sq. min.
82	MRD210	7	N	Si	X83a		BVCEO-50V;ICEO-25nA at 25deg C;SICE-.4uA/lum/ft-2min;LS-.8um typ.
83	MRD250	7	N	Si	X83a		BVCEO-50V;ICEO-25nA at 25deg C;SICE-.8uA/lum/ft-2min;LS-.8um typ.
84	OCP71	7	P	Ge	R9		Pt-50mW; BVCEO-25V; IC-20mA; Sens-.30A/lm
85#	OS13	7	P	Ge	X1		Pc-15mW max; BVCBO-30; Ic-2mA max.
86#	OS15	7	N	Si	X1		Pc-30mW max;BVCEO-30Vmax;Ic-200uA max; Photo-Sens-1uA/500 Lumen.
87#	OS16	7	N	Si	X1		Pc-30mW max;BVCEO-30Vmax;Ic-200uA max; Photo-Sens-4uA/500 Lumen.
88#	OS17	7	N	Si	X1		Pc-30mW max;BVCEO-30Vmax;Ic-200uA max; Photo-Sens-7uA/500 Lumen.
89	PD3L	7		Ge			Pc-.10W max; BVCBO-50V; IC-5.0ma max.
90	PD6	7		Ge			Pc-20mW max; BVCBO-50V; IC-5.0ma max.
91	PFN3066*	7	N-E	Si	TO18	DB	IGSS(light) 3.onA/fc;ID(light) 2.0uA/fc.
92	PFN3069*	7	N-E	Si	TO18	DB	IGSS(light) 8.0nA/fc;ID(light) 14uA/fc.
93	PFN3458*	7	N-E	Si	TO18	DB	IGSS(light) 10nA/fc;ID(light) 35uA/fc.
94#	PH244N*	7	N-PEΔ	Si	X8f	DBØ	Pd 300mW; IGSS(light)15nA/FC;ID(light)100uA/FC.
95	TIL58	7	NPLΔ	Si	X69a		Pd-50mW;ID-25nAmax;IL-1.0mAmin;tr-2.0usec;BVceo-50V;BVeco-8.0V;tf-15usec.
96	TIL78	7	N	Si			Pt 50mW;IL 1.0mA min;ID 25nA max;tr 1.5us typ;tf 15us typ;BVCEO 50V min;BVECO 7.0Vmin
97	3N25	8	PGD	Ge			Pc-25mW max; fab-200Mc; Ic-2.0mA max.
98	3N35A	8	N	Si	TO12		Pd-.125W;Rsat-300 ohms;ries-20 ohms min;Coep-3.0pf
99	3N56	8	N-Δ	Si	TO5		Pc-.15W max; BVCBO-18V; IC-30ma max.
100	3N57	8	N-Δ	Si	TO5		Pc-.15W max; BVCBO-18V; IC-30ma max.
101#	3S001	8	N-D	Si			Pc-125mW;BVCBO-30V;Ic-10mA; Gain 18 db ICBO-.2uA
102#	3S002	8	N-GD	Si	TO12		Pc-.125W max; fab-100Mc; BVCBO-30V; Ic-10mA max.
103#	3S003	8	N-D	Si			Pc-125mW;BVCBO-30V;Ic-10mA; Gain 20 db ICBO-.2uA
104#	3S004	8	N-GD S	i	si TO1	2	Pc-.125W max; fab-150Mc; BVCBO-30V; Ic-10mA max.
105	GTA3	8	P	Ge			Pc-2.5mW; fab-200Mc; BVCBO-15V; Ic-2.0mA max.
106	JAN2N489	9	P-N	Si	R33		Pc-.45W max;VE-60V max;ISR-.62 max;RBBO-6.8k Ω max.
107	JAN2N490	9	P-N	Si	R33		Pc-.45W max;VE-60V max;ISR-.62 max;RBBO-6.8k Ω max.
108	JAN2N491	9	P-N	Si	R33		Pc-.45W max;VE-60V max;ISR-.68 max;RBBO-6.8k Ω max.
109	JAN2N492	9	P-N	Si	R33		Pc-.45W max;VE-60V max;ISR-.68 max;RBBO-6.8k Ω max.
110	JAN2N493	9	P-N	Si	R33		Pc-.45W max;VE-60V max;ISR-.75 max;RBBO-6.8k Ω max.

SYMBOLS AND CODES EXPLAINED IN INTERPRETER